

Dallas Semiconductor IME 3Q01

DS2118	5508	0	0
DS16A43	9090	40	4004
DS1050	9983	11	1102
Totals for 0.6um:	14598	40	2740
DS1232	9989	3	300
DS1780	6704	2	298
DS21T07	9989	0	0
Totals for 0.8um:	26682	5	187

Goal = 300 ppm

Ken Wendel 4/20/01

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Part No.	Qty	Fail Mechanism
DS2118M	3	Could not resolve Failure
DS21352	3	Could resolve Failure
	1	In Analysis
DS21554	10	In Analysis
DS80CH11	66	In Analysis
DS1232	1	Isolated to SV Osc Circuit. FM not resolved
	2	Gate Oxide defect
DS87C520	11	Gate Oxide defect
	3	In Analysis
DS2154	21	In Analysis